SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

SLLS151D - DECEMBER 1988 - REVISED APRIL 2003

 Meet or Exceed the Requirements of TIA/EIA-232-F and ITU Recommendation V 28

- Very Low Power Consumption . . .5 mW Typ
- Wide Driver Supply Voltage . . . ±4.5 V to ±15 V
- Driver Output Slew Rate Limited to 30 V/μs Max
- Receiver Input Hysteresis . . . 1000 mV Typ
- Push-Pull Receiver Outputs
- On-Chip Receiver 1-μs Noise Filter

SN65C1154...N PACKAGE SN75C1154 . . . DW. N. OR NS PACKAGE (TOP VIEW) 20 🛮 V_{CC} V_{DD} 1RA 🛮 2 19 1 1RY 18 🛮 1DA 1DY [] 3 2RA **∏** 4 17 **∏** 2RY 2DY **∏** 5 16 2DA 15 3RY 3RA 🛮 6 3DY 🛮 7 14 ¶ 3DA 4RA **∏** 8 13 **∏** 4RY 12 **]** 4DA 4DY 🛮 9 11 GND

description/ordering information

The SN65C1164 and SN75C1154 are low-power BiMOS devices containing four independent drivers and receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). These devices are designed to conform to TIA/EIA-232-F. The drivers and receivers of the SN65C1154 and SN75C1154 are similar to those of the SN75C188 quadruple driver and SN75C189A quadruple receiver, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ μ s and the receivers have filters that reject input noise pulses of shorter than 1 μ s. Both these features eliminate the need for external components.

The SN65C1154 and SN75C1154 have been designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in these devices interface to single inputs of peripheral devices such as ACEs, UARTs, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN65C1154 and SN75C1154 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

ORDERING INFORMATION

TA	PACKAC	e†	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	PDIP (N)	Tube of 20	SN65C1154N	SN65C1154N
	PDIP (N)	Tube of 20	SN75C1154N	SN75C1154N
0°C to 70°C	SOIC (DW)	Tube of 25	SN75C1154DW	SN75C1154
0 0 10 70 0	SOIC (DVV)	Reel of 2500	SN75C1154DWR	3117301134
	SOP (NS)	Reel of 2000	SN75C1154NSR	SN75C1154

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



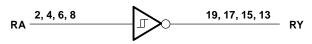
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



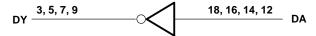
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logic diagram (positive logic)

Typical of Each Receiver

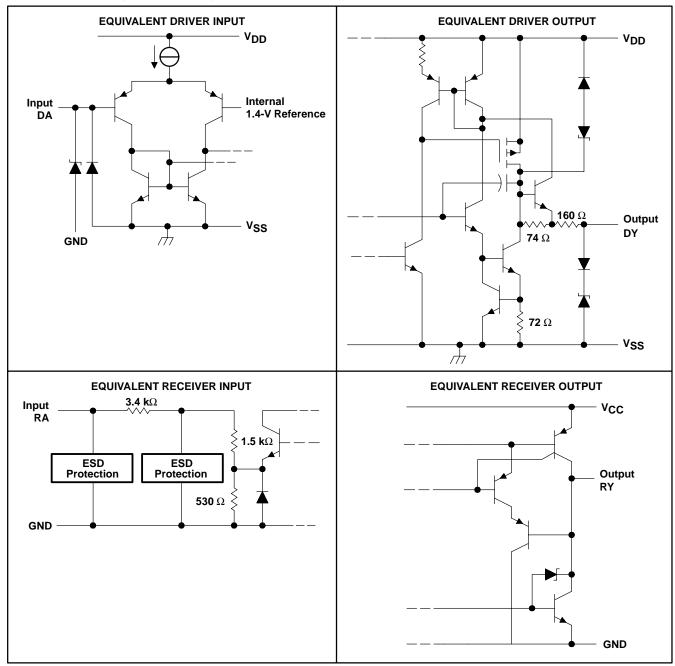


Typical of Each Driver





schematics of inputs and outputs



Resistor values shown are nominal.

SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage: V _{DD} (see Note 1)	
V _{SS}	
V _{CC}	7 V
Input voltage range, V _I : Driver	V_{SS} to V_{DD}
Receiver	
Output voltage range, VO:Driver	
Receiver	0.3 V to (V _{CC} + 0.3 V)
Package thermal impedance, θ_{JA} (see Notes 2 and 3):	DW package 58°C/W
•	N package 69°C/W
	NS package 60°C/W
Operating virtual junction temperature, T _{.1}	
Storage temperature range, T _{stq}	
Lead temperature 1,6 mm (1/16 inch) from case for 10	seconds 260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage s are with respect to the network GND terminal.
 - 2. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

			MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage		4.5	12	15	V
VSS	Supply voltage		-4.5	-12	-15	V
Vcc	Supply voltage		4.5	5	6	V
١/،	Input voltage	Driver	V _{SS} + 2		V_{DD}	V
٧ _I	input voitage	Receiver			±25	٧
VIH	High-level input voltage	Driver	2			V
V _{IL}	Low-level input voltage	Driver			0.8	٧
ЮН	High-level output current	Receiver			-1	mA
loL	High-level output current	Receiver			3.2	mA
т.	Operating free-air temperature	SN65C1154	-40		85	°C
TA	Operating nee-all temperature	SN75C1154	0		70	



DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS		MIN	TYP†	MAX	UNIT
V	High-level output voltage	$V_{IL} = 0.8 V$,	$R_L = 3 k\Omega$,	$V_{DD} = 5 V$,	$V_{SS} = -5 V$	4	4.5		V
VOH	nigri-level output voltage	See Figure 1	_	$V_{DD} = 12 V$,	$V_{SS} = -12 \text{ V}$	10	10.8		V
Voi	Low-level output voltage	V _{IH} = 2 V,	$R_L = 3 k\Omega$,	$V_{DD} = 5 V$,	V _{SS} = -5 V		-4.4	-4	V
VOL	(see Note 4)	See Figure 1		V _{DD} = 12 V,	$V_{SS} = -12 \text{ V}$		-10.7	-10	V
lіН	High-level input current	V _I = 5 V,	See Figure 2					1	μΑ
IJL	Low-level input current	$V_{I} = 0,$	See Figure 2					-1	μΑ
los(H)	High-level short-circuit output current‡	V _I = 0.8 V,	$V_O = 0$ or V_{SS} ,	See Figure 1		-7.5	-12	-19.5	mA
IOS(L)	Low-level short-circuit output current‡	V _I = 2 V,	$V_O = 0$ or V_{DD} ,	See Figure 1		7.5	12	19.5	mA
Inn	Supply current from VDD	No load,		$V_{DD} = 5 V$,	$V_{SS} = -5 V$		115	250	^
IDD	Зарріў сапені поні ў рр	All inputs at 2 \	/ or 0.8 V	$V_{DD} = 12 V$,	$V_{SS} = -12 \text{ V}$		115	250	μΑ
laa	Supply current from Voc	No load,	_	$V_{DD} = 5 V$,	V _{SS} = -5 V		-115	-250	
ISS	Supply current from VSS	All inputs at 2 \	All inputs at 2 V or 0.8 V		$V_{SS} = -12 \text{ V}$		-115	-250	μΑ
r _o	Output resistance	$V_{DD} = V_{SS} = V_{DD}$	$V_{CC} = 0$, $V_{O} = -1$	2 V to 2 V,	See Note 5	300	400	·	Ω

[†] All typical values are at $T_A = 25^{\circ}C$.

NOTES: 4. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

5. Test conditions are those specified by TIA/EIA-232-F.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V ±10%, T_A = 25°C (see Figure 3)

	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output§	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	CL = 15 pF		1.2	3	μs
tPHL	Propagation delay time, high- to low-level output§	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	CL = 15 pF		2.5	3.5	μs
tTLH	Transition time, low- to high-level output¶	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	CL = 15 pF	0.53	2	3.2	μs
tTHL	Transition time, high- to low-level output¶	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	CL = 15 pF	0.53	2	3.2	μs
tTLH	Transition time, low- to high-level output#	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	C _L = 2500 pF		1	2	μs
tTHL	Transition time, high- to low-level output#	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	C _L = 2500 pF		1	2	μs
SR	Output slew rate	$R_L = 3 \text{ to } 7 \text{ k}\Omega$	CL = 15 pF	4	10	30	V/μs

[§] tpHL and tpLH include the additional time due to on-chip slew rate control and are measured at the 50% points.



[‡] Not more than one output should be shorted at one time.

[¶] Measured between 10% and 90% points of output waveform

[#] Measured between 3 V and -3 V points of output waveform (TIA/EIA-232-F conditions) with all unused inputs tied either high or low

RECEIVER SECTION

electrical characteristics over operating free-air temperature range, $V_{DD} = 12 \text{ V}$, $V_{SS} = -12 \text{ V}$, V_{CC} = 5 V \pm 10% (unless otherwise noted)

	PARAMETER	TEST CON	IDITIONS	MIN	TYP†	MAX	UNIT
V _{IT+}	Positive-going input threshold voltage	See Figure 5		1.7	2.1	2.55	٧
V _{IT} –	Negative-going input threshold voltage	See Figure 5		0.65	1	1.25	٧
V _{hys}	Input hysteresis voltage (V _{IT+} - V _{IT-})			600	1000		mV
		$V_I = 0.75 \text{ V}, \qquad I_{OH} = -20 \mu\text{A},$	See Figure 5 and Note 6	3.5			
\/o	High lovel output voltage	V 0.75 V 1 4 4	V _{CC} = 4.5 V	2.8	4.4		V
VOH	High-level output voltage	$V_I = 0.75 \text{ V}, I_{OH} = -1 \text{ mA},$ See Figure 5	V _{CC} = 5 V	3.8	4.9		V
		occ rigure o	V _{CC} = 5.5 V	4.3	5.4		
VOL	Low-level output voltage	$V_I = 3 V$, $I_{OL} = 3.2 \text{ mA}$,	See Figure 5		0.17	0.4	V
1	High lovel input overent	V _I = 25 V		3.6	4.6	8.3	mA
lΗ	High-level input current	V _I = 3 V		0.43	0.55	1	mA
1	Low lovel input ourrent	V _I = -25 V		-3.6	- 5	-8.3	mA
¹IL	Low-level input current	V _I = −3 V		-0.43	-0.55	-1	ША
IOS(H)	Short-circuit output at high level	$V_I = 0.75 \text{ V}, V_O = 0,$	See Figure 4		-8	-15	mA
IOS(L)	Short-circuit output at low level	$V_I = V_{CC},$ $V_O = V_{CC},$	See Figure 4		13	25	mA
loo	Supply current from V _{CC}	No load,	$V_{DD} = 5 \text{ V}, V_{SS} = -5 \text{ V}$		400	600	μА
ICC	Subbis causin upun ACC	All inputs at 0 or 5 V	$V_{DD} = 12 \text{ V}, V_{SS} = -12 \text{ V}$		400	600	μΑ

 † All typical values are at $T_A = 25^{\circ}$ C. NOTE 6: If the inputs are left unconnected, the receiver interprets this as an input low and the receiver outputs will remain in the high state.

switching characteristics, V_{DD} = 12 V, V_{SS} = -12 V, V_{CC} = 5 V \pm 10%, T_A = 25°C

	PARAMETER	Т	EST CONDITIO	MIN	TYP	MAX	UNIT	
tPLH	Propagation delay time, low- to high-level output	C _L = 50 pF,	$R_L = 5 k\Omega$,	See Figure 6		3	4	μs
tPHL	Propagation delay time, high- to low-level output	C _L = 50 pF,	R _L = 5 kΩ,	See Figure 6		3	4	μs
tTLH	Transition time, low- to high-level output	$C_L = 50 \text{ pF},$	$R_L = 5 k\Omega$,	See Figure 6		300	450	ns
tTHL	Transition time, high- to low-level output	C _L = 50 pF,	$R_L = 5 k\Omega$,	See Figure 6		100	300	ns
t _w (N)	Duration of longest pulse rejected as noise‡	C _L = 50 pF,	$R_L = 5 \text{ k}\Omega$		1		4	μs

 $[\]ddagger$ The receiver ignores any positive- or negative-going pulse that is less than the minimum value of $t_{W(N)}$ and accepts any positive- or negative-going pulse greater than the maximum of $t_{W(N)}$.



PARAMETER MEASUREMENT INFORMATION

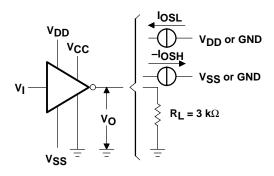


Figure 1. Driver Test Circuit $(V_{OH}, V_{OL}, I_{OSL}, I_{OSH})$

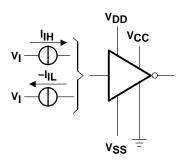
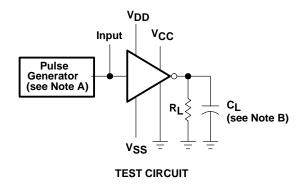
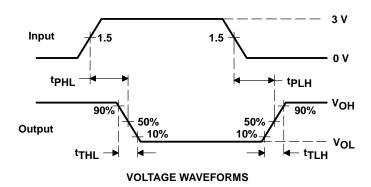


Figure 2. Driver Test Circuit (I_{IL}, I_{IH})





NOTES: A. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_f = t_f < 50 ns.

B. C_L includes probe and jig capacitance.

Figure 3. Driver Test Circuit and Voltage Waveforms

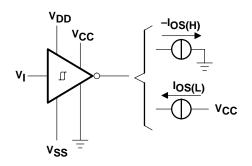


Figure 4. Receiver Test Circuit (I_{OSH}, I_{OSL})

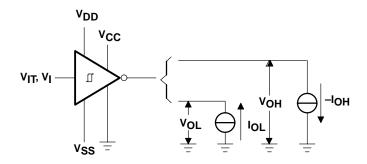
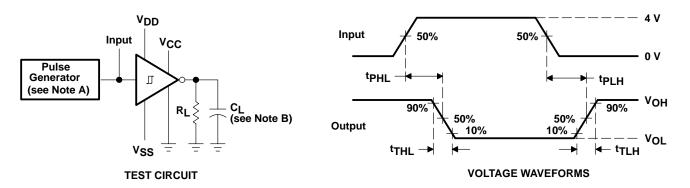


Figure 5. Receiver Test Circuit (V_{IT}, V_{OL}, V_{OH})

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_Γ = t_f < 50 ns.
 - B. C_L includes probe and jig capacitance.

Figure 6. Receiver Test Circuit and Voltage Waveforms





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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C1154N	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN65C1154N	Samples
SN75C1154DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1154	Samples
SN75C1154DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1154	Samples
SN75C1154N	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75C1154N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75C1154DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN75C1154DWR	SOIC	DW	20	2000	350.0	350.0	43.0	

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C1154N	N	PDIP	20	20	506	13.97	11230	4.32
SN75C1154DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
SN75C1154N	N	PDIP	20	20	506	13.97	11230	4.32

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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